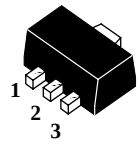
WEITRON

2SC4672

NPN EPITAXIAL PLANAR TRANSISTOR

Lead(Pb)-Free

1. BASE
2. COLLECTOR
3. EMITTER



SOT-89

Features:

* Low saturation voltage, typically
  V_{CE}(sat) =0.35V at I_C/I_B=1A/50mA.
* Excellent DC current gain characteristics.

Mechanical Data:

* Case : Molded Plastic

ABSOLUTE MAXIMUM RATINGS(T_A=25ºC Unless Otherwise Noted)

Rating	Symbol	Value	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	50	V
Collector to Base Voltage	V_{EBO}	6	V
Collector Current (DC)	I_C	2.0	A
Total Device Disspation T_A=25°C	P_D	2	W
Junction Temperature	Tj	+150	˚C
Storage Temperature	Tstg	-55 to +150	˚C

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage I_C=50μA, I_E=0	BV_{CBO}	60	-	-	V
Collector-Emitter Breakdown Voltage I_C=1mA, I_B=0	BV_{CEO}	50	-	-	V
Emitter-Base Breakdown Voltage I_E=50μA, I_C=0	BV_{EBO}	6.0	-	-	V
Collector Cut-Off Current V_{CB}=60V, I_E=0	I_{CBO}	-	-	0.1	μA
Emitter-Cut-Off Current V_{EB}=5V, I_C=0	I_{EBO}	-	-	0.1	μA

ON CHARACTERISTICS*

DC Current Gain V_{CE}=2V, I_C=500mA	h_{FE}	82	-	270	-
Collector-Emitter Saturation Voltage I_C=1A, I_B=50mA	$V_{CE(sat)}$	-	-	0.35	V

*Pulse Test: Pluse Width ≤ 380μs, Duty Cycle ≤ 2%.

DYNAMIC CHARACTERISTICS

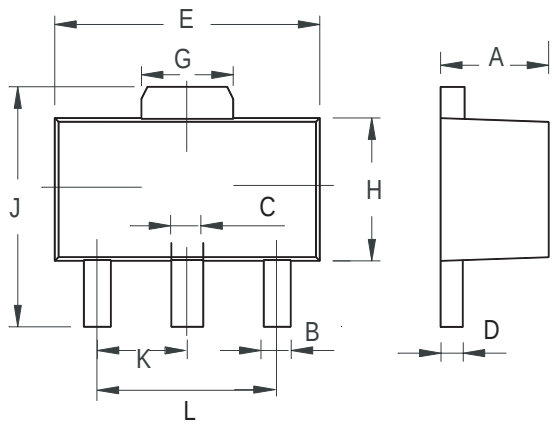
Transition Frequency V_{CE}=2V, I_E=500mA, f=100MHz	f_T	-	210	-	MHz
Output Capacitance V_{CB}=10V, I_E=0, f=1MHz	C_{ob}	-	25	-	pF

CLASSIFICATION OF h_{FE}

Rank	P	Q
Range	82-180	120-270
Marking	DKP	DKQ

SOT-89 Outline Dimensions

unit:mm



SOT-89		
Dim	**Min**	**Max**
A	1.400	1.600
B	0.320	0.520
C	0.360	0.560
D	0.350	0.440
E	4.400	4.600
G	1.400	1.800
H	2.300	2.600
J	3.940	4.250
K	1.500TYP	
L	2.900	3.100